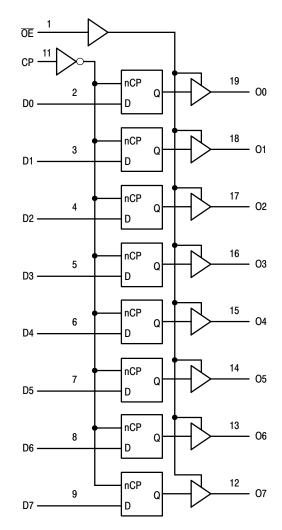


Figure 1. Pinout: 20-Lead (Top View)

### **PIN NAMES**

Pins	Function
OE	Output Enable Input
CP	Clock Pulse Input
D0-D7	Data Inputs
00-07	3-State Outputs





#### **TRUTH TABLE**

	INPUTS		INTERNAL LATCHES	OUTPUTS	
ŌE	СР	Dn	Q	On	OPERATING MODE
L	$\stackrel{\frown}{\leftarrow}$	l h	LH	L H	Load and Read Register
L	1	Х	NC	NC	Hold and Read Register
Н	¢	Х	NC	Z	Hold and Disable Outputs
H H	$\stackrel{}{\leftarrow}$	l h	L H	Z Z	Load Internal Register and Disable Outputs

Н High Voltage Level =

h High Voltage Level One Setup Time Prior to the Low-to-High Clock Transition =

L = Low Voltage Level

Low Voltage Level One Setup Time Prior to the Low-to-High Clock Transition L =

NC = No Change

Х High or Low Voltage Level and Transitions are Acceptable =

Z ↑ = High Impedance State

Low-to-High Transition =

≄ = Not a Low-to-High Transition; For I<sub>CC</sub> Reasons, DO NOT FLOAT Inputs

## **MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_0 \le +7.0$	Output in 3–State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
Ι <sub>ΟΚ</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	$V_{O} > V_{CC}$	mA
IO	DC Output Source/Sink Current	±50		mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.
1. Output in HIGH or LOW State. I<sub>O</sub> absolute maximum rating must be observed.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Paramete	er	Min	Тур	Max	Unit
V <sub>CC</sub>	Supply Voltage	Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
V <sub>O</sub>	Output Voltage	(HIGH or LOW State) (3–State)	0 0		V <sub>CC</sub> 5.5	V
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 3.0 V	/ – 3.6 V			-24	mA
I <sub>OL</sub>	LOW Level Output Current, $V_{CC} = 3.0$ V	′ – 3.6 V			24	mA
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 2.7 V	/ - 3.0 V			-12	mA
I <sub>OL</sub>	LOW Level Output Current, $V_{CC} = 2.7$ V	′ – 3.0 V			12	mA
T <sub>A</sub>	Operating Free–Air Temperature		-40		+85	°C
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate, VIN fr	om 0.8 V to 2.0 V, V <sub>CC</sub> = 3.0 V	0		10	ns/V

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LCX574DWR2	SOIC-20	1000 Tape & Reel
MC74LCX574DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LCX574DT	TSSOP-20*	75 Units / Rail
MC74LCX574DTR2	TSSOP-20*	2000 Tape & Reel
MC74LCX574MEL	SOEIAJ-20	2000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 \*This package is inherently Pb–Free.

# DC ELECTRICAL CHARACTERISTICS

			T <sub>A</sub> = −40°C		
Symbol	Characteristic	Condition	Min	Max	Unit
V <sub>IH</sub>	HIGH Level Input Voltage (Note 2)	$2.7 \text{ V} \leq \text{V}_{\text{CC}} \leq 3.6 \text{ V}$	2.0		V
V <sub>IL</sub>	LOW Level Input Voltage (Note 2)	$2.7 \text{ V} \leq \text{V}_{\text{CC}} \leq 3.6 \text{ V}$		0.8	V
V <sub>OH</sub>	HIGH Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OH} = -100 \mu\text{A}$	V <sub>CC</sub> – 0.2		V
		$V_{CC} = 2.7 \text{ V}; \text{ I}_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -18 \text{ mA}$	2.4		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -24 mA	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	2.7 V $\leq$ V_{CC} $\leq$ 3.6 V; I_{OL} = 100 $\mu A$		0.2	V
		V <sub>CC</sub> = 2.7 V; I <sub>OL</sub> = 12 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 16 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 24 mA		0.55	
l <sub>l</sub>	Input Leakage Current	$2.7 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}; \text{ 0 V} \leq \text{V}_{\text{I}} \leq 5.5 \text{ V}$		±5.0	μΑ
I <sub>OZ</sub>	3-State Output Current	$2.7 \leq V_{CC} \leq 3.6 \text{ V}; \ 0 \text{ V} \leq V_O \leq 5.5 \text{ V}; \\ V_I = V_{IH} \text{ or } V_{IL}$		±5.0	μΑ
I <sub>OFF</sub>	Power-Off Leakage Current	$V_{CC}$ = 0 V; V <sub>1</sub> or V <sub>O</sub> = 5.5 V		10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$2.7 \leq V_{CC} \leq 3.6$ V; VI = GND or V_{CC}		10	μA
		$2.7 \leq V_{CC} \leq 3.6$ V; $3.6 \leq V_{I}$ or $V_{O} \leq 5.5$ V	1	±10	μA
$\Delta I_{CC}$	Increase in I <sub>CC</sub> per Input	$2.7 \le V_{CC} \le 3.6 \text{ V}; \text{ V}_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

2. These values of V<sub>I</sub> are used to test DC electrical characteristics only.

# AC CHARACTERISTICS ( $t_R = t_F = 2.5 \text{ ns}$ ; $C_L = 50 \text{ pF}$ ; $R_L = 500 \Omega$ )

				Lin	nits		
				T <sub>A</sub> = -40°0	C to +85°C		
			V <sub>CC</sub> = 3.0	) V to 3.6 V	V <sub>CC</sub> =	= 2.7 V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit
f <sub>max</sub>	Clock Pulse Frequency	1	150				MHz
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay CP to On	1	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to HIGH and LOW Levels	2	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time from HIGH and LOW Levels	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	ns
t <sub>s</sub>	Setup TIme, HIGH or LOW Dn to CP	1	2.5		2.5		ns
t <sub>h</sub>	Hold TIme, HIGH or LOW Dn to CP	1	1.5		1.5		ns
tw	CP Pulse Width, HIGH or LOW	3	3.3		3.3		ns
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 3)			1.0 1.0			ns

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

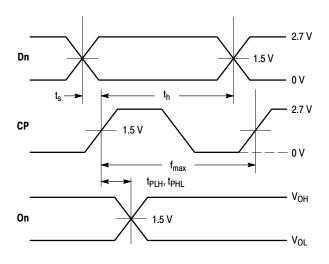
### DYNAMIC SWITCHING CHARACTERISTICS

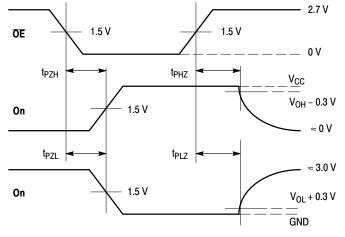
			T,	T <sub>A</sub> = +25°C		
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 4)	$V_{CC}$ = 3.3 V, $C_{L}$ = 50 pF, $V_{IH}$ = 3.3 V, $V_{IL}$ = 0 V		0.8		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 4)	$V_{CC}$ = 3.3 V, $C_L$ = 50 pF, $V_{IH}$ = 3.3 V, $V_{IL}$ = 0 V		0.8		V

 Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

# **CAPACITIVE CHARACTERISTICS**

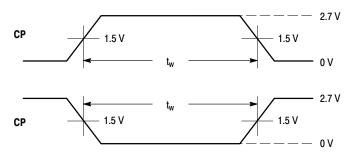
Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	7	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	25	pF





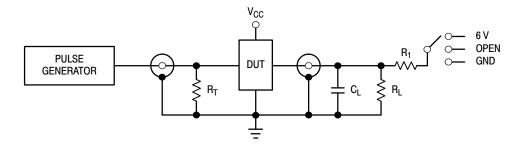
# WAVEFORM 1 – PROPAGATION DELAYS, SETUP AND HOLD TIMES $t_R$ = $t_F$ = 2.5 ns, 10% to 90%; f = 1 MHz; $t_W$ = 500 ns

WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES  $t_R = t_F = 2.5$  ns, 10% to 90%; f = 1 MHz;  $t_W = 500$  ns



 $\label{eq:WaveForm 3 - PULSE WIDTH} \begin{array}{l} \text{WaveForm 3 - PULSE WIDTH} \\ t_{R} = t_{F} = 2.5 \text{ ns (or fast as required) from 10% to 90%;} \\ \text{Output requirements: } V_{OL} \leq 0.8 \text{ V}, V_{OH} \geq 2.0 \text{ V} \end{array}$ 

Figure 3. AC Waveforms



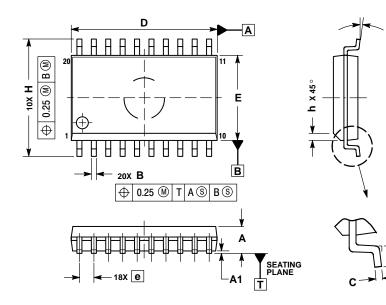
TEST	SWITCH
t <sub>PLH</sub> , t <sub>PHL</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	6 V
Open Collector/Drain tPLH and tPHL	6 V
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

 $C_L = 50 \text{ pF}$  or equivalent (Includes jig and probe capacitance)  $R_L = R_1 = 500 \Omega$  or equivalent  $R_T = Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

Figure 4. Test Circuit

# PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G** 

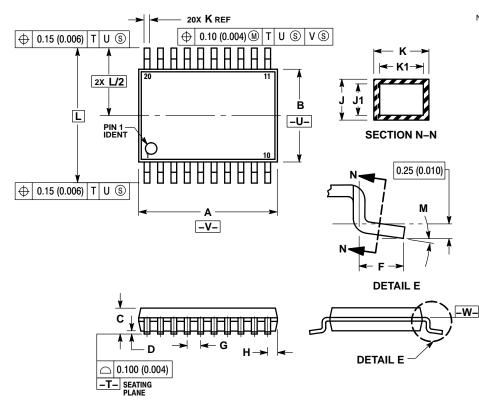


NOTES:

- 1. 2.
- DIMENSIONS ARE IN MILLIMETERS. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD 3. PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B 5. DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
C	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

TSSOP-20 **DT SUFFIX** CASE 948E-02 ISSUE B



NOTES:

DITES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SUDE

SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER

SIDE. 5. DIMENSION K DOES NOT INCLUDE 5. DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 5. TERMINAL NUMBERS ARE SHOWN

6.

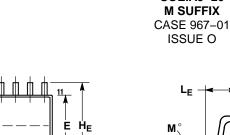
FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-. 7

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
Μ	0°	8°	0 °	8°	

#### PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** 

ISSUE O



10

0.10 (0.004)

 $\cap$ 

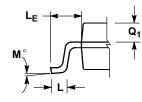
Z

h

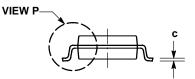
0.13 (0.005) 🕅

e

 $\oplus$ 



DETAIL P



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI 1. Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- 2 CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) 3
- PER SIDE. TERMINAL NUMBERS ARE SHOWN FOR 4
- REFERENCE ONLY. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE 5 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
Μ	0 °	10 °	0 °	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.81		0.032

ON Semiconductor and in the registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or the rights of others. SCILLC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.